MJE243 - NPN, MJE253 - PNP

Complementary Silicon Power Plastic Transistors

These devices are designed for low power audio amplifier and low−current, high−speed switching applications.

Features

- High Collector−Emitter Sustaining Voltage − $V_{CEO(sus)}$ = 100 Vdc (Min)
- High DC Current Gain @ I_C = 200 mAdc h_{FE} = 40 − 200 = 40 − 120
- Low Collector−Emitter Saturation Voltage − $V_{CE(sat)}$ = 0.3 Vdc (Max) @ I_C = 500 mAdc
- High Current Gain Bandwidth Product − f_T = 40 MHz (Min) @ I_C = 100 mAdc
- Annular Construction for Low Leakages I_{CBO} = 100 nAdc (Max) @ Rated V_{CB}
- Pb−Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector−Emitter Voltage	V_{CEO}	100	Vdc
Collector−Base Voltage	V_{CB}	100	Vdc
Emitter−Base Voltage	V_{EB}	7.0	Vdc
Collector Current − Continuous − Peak	I_C	4.0 8.0	Adc
Base Current	I_B	10	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	15 120	W mW/°C
Total Power Dissipation @ T_A = 25°C Derate above 25°C	P_D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction−to−Case	θ_{JC}	8.34	°C/W
Thermal Resistance, Junction−to−Ambient	θ_{JA}	83.4	°C/W

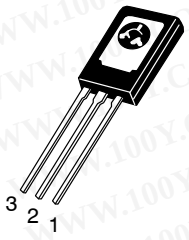
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor®

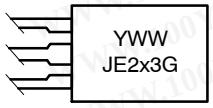
http://onsemi.com

4.0 AMPERES POWER TRANSISTORS COMPLEMENTARY SILICON 100 VOLTS, 15 WATTS



TO−225
CASE 77
STYLE 1

MARKING DIAGRAM



Y = Year
WW = Work Week
JE2x3 = Device Code
x = 4 or 5
G = Pb−Free Package

ORDERING INFORMATION

Device	Package	Shipping
MJE243	TO−225	500 Units/Box
MJE243G	TO−225 (Pb−Free)	500 Units/Box
MJE253	TO−225	500 Units/Box
MJE253G	TO−225 (Pb−Free)	500 Units/Box

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage (I_C = 10 mAdc, I_B = 0)	$V_{CEO(sus)}$	100	–	V
Collector Cutoff Current (V_{CB} = 100 Vdc, I_E = 0) (V_{CE} = 100 Vdc, I_E = 0, T_C = 125°C)	I_{CBO}	– –	0.1 0.1	μA mA
Emitter Cutoff Current (V_{BE} = 7.0 Vdc, I_C = 0)	I_{EBO}	–	0.1	μAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = 200 mAdc, V_{CE} = 1.0 Vdc) (I_C = 1.0 Adc, V_{CE} = 1.0 Vdc)	h_{FE}	40 15	180 –	–
Collector–Emitter Saturation Voltage (I_C = 500 mAdc, I_B = 50 mAdc) (I_C = 1.0 Adc, I_B = 100 mAdc)	$V_{CE(sat)}$	– –	0.3 0.6	V
Base–Emitter Saturation Voltage (I_C = 2.0 Adc, I_B = 200 mAdc)	$V_{BE(sat)}$	–	1.8	V
Base–Emitter On Voltage (I_C = 500 mAdc, V_{CE} = 1.0 Vdc)	$V_{BE(on)}$	–	1.5	V
DYNAMIC CHARACTERISTICS				
Current–Gain – Bandwidth Product (I_C = 100 mAdc, V_{CE} = 10 Vdc, f_{test} = 10 MHz)	f_T	40	–	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 0.1 MHz)	C_{ob}	–	50	pF

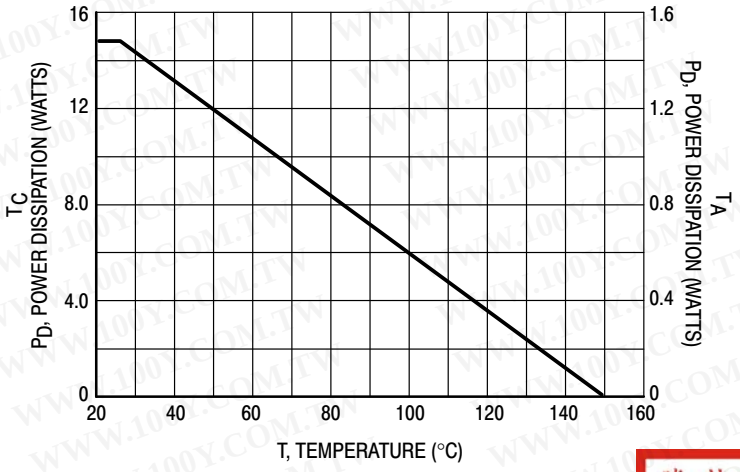
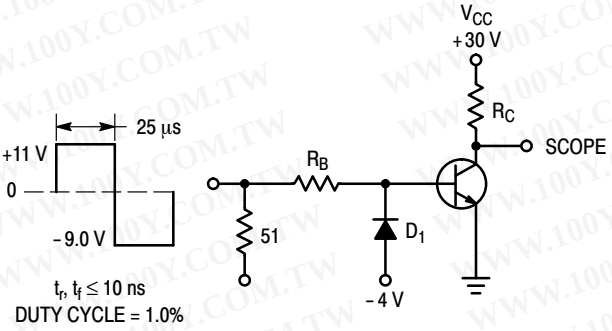


Figure 1. Power Derating



R_B and R_C VARIED TO OBTAIN DESIRED CURRENT LEVELS
D_1 MUST BE FAST RECOVERY TYPE, e.g.:
1N5825 USED ABOVE $I_B \approx$ 100 mA
MSD6100 USED BELOW $I_B \approx$ 100 mA
FOR PNP TEST CIRCUIT, REVERSE ALL POLARITIES

Figure 2. Switching Time Test Circuit

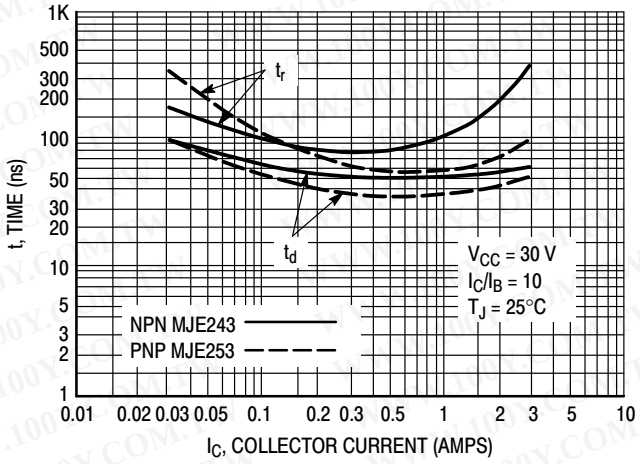


Figure 3. Turn–On Time

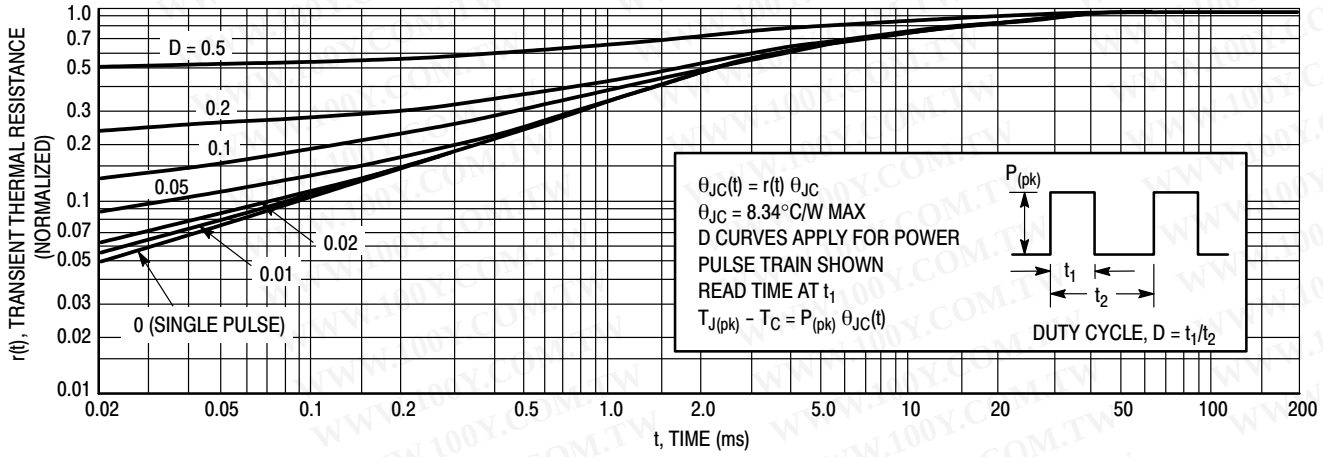


Figure 4. Thermal Response

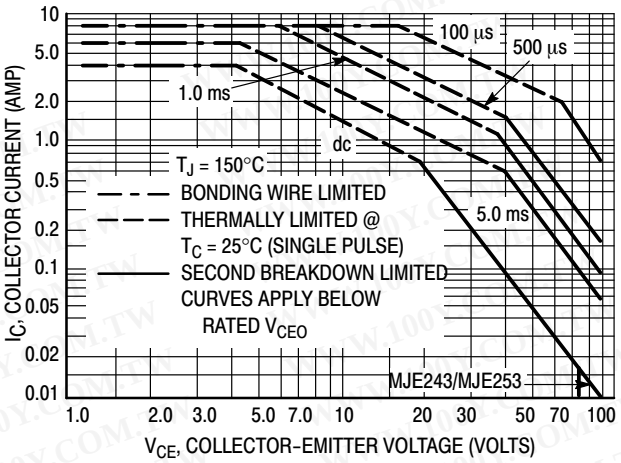


Figure 5. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)}$ = 150°C; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150°C$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

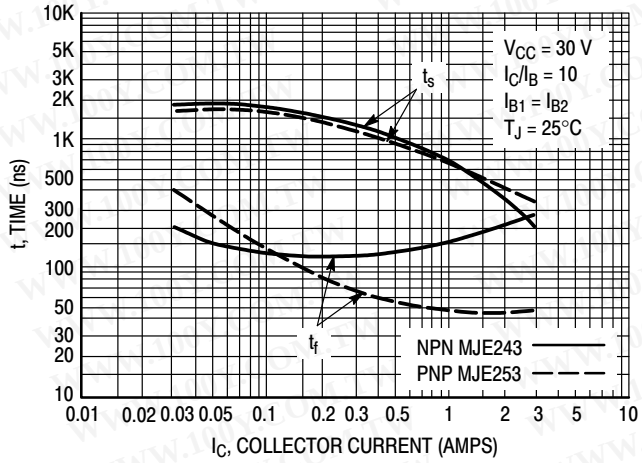


Figure 6. Turn–Off Time

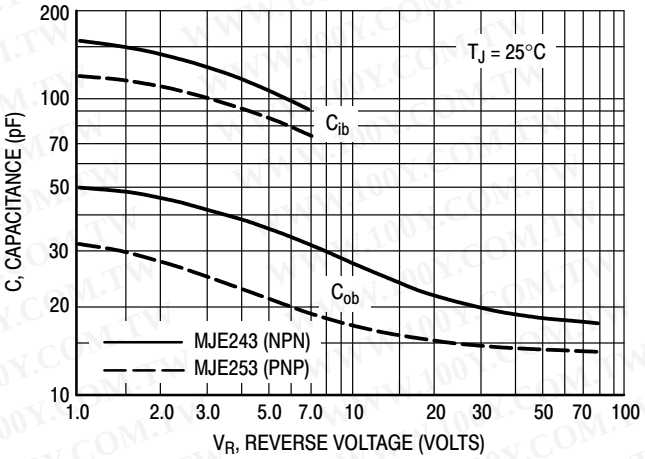
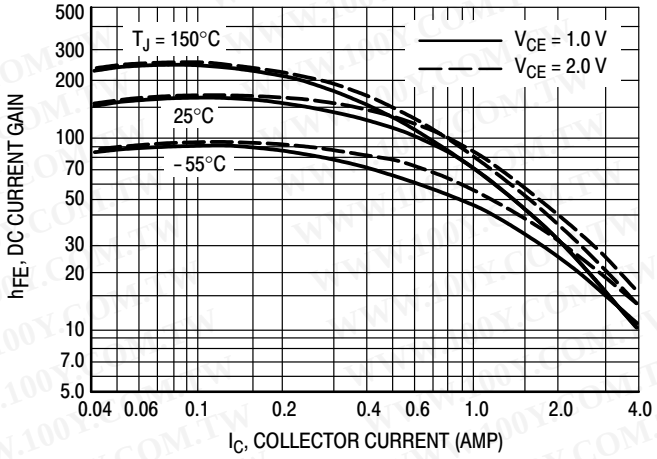


Figure 7. Capacitance

NPN
MJE243



PNP
MJE253

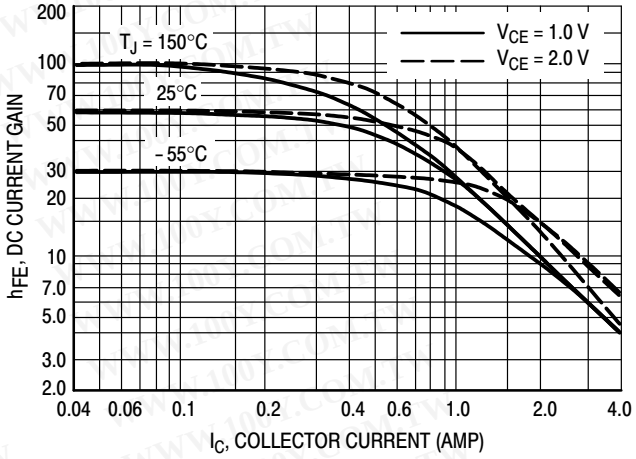
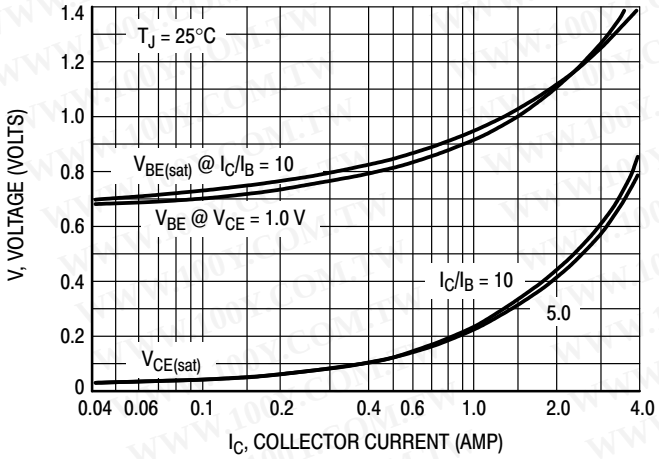


Figure 8. DC Current Gain



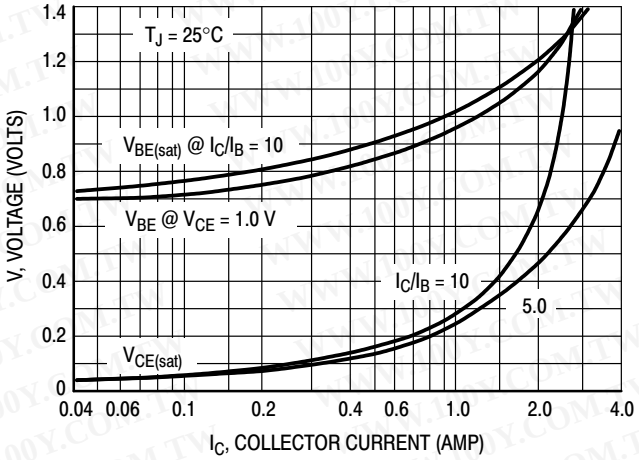
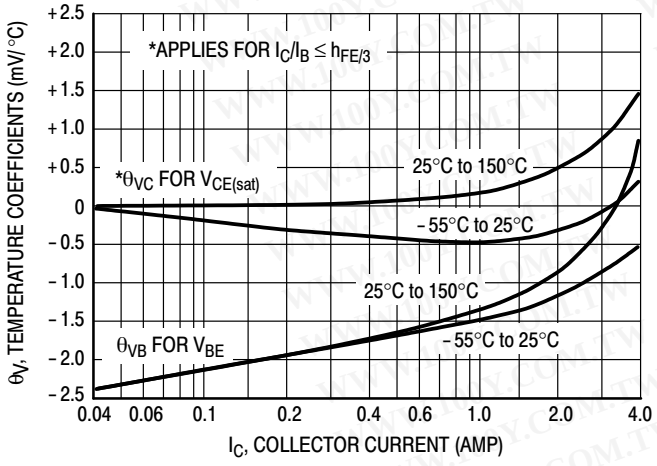


Figure 9. “On” Voltages



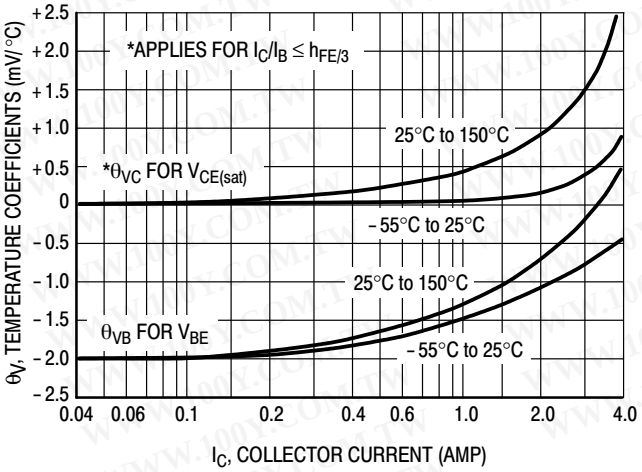
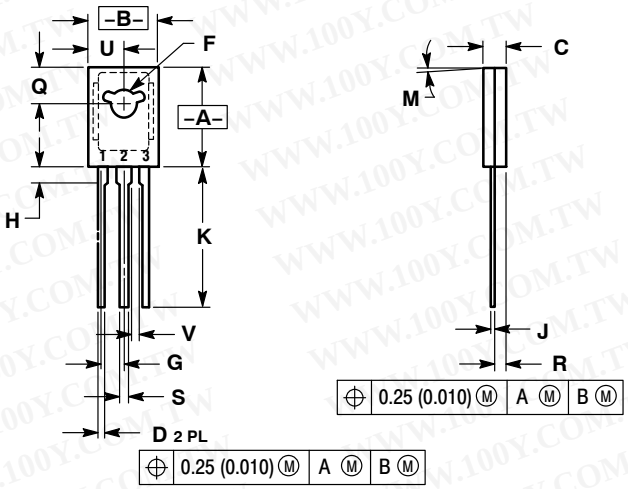


Figure 10. Temperature Coefficients

PACKAGE DIMENSIONS

TO–225
CASE 77–09
ISSUE Z



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 077–01 THRU –08 OBSOLETE, NEW STANDARD 077–09.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.425	0.435	10.80	11.04
B	0.295	0.305	7.50	7.74
C	0.095	0.105	2.42	2.66
D	0.020	0.026	0.51	0.66
F	0.115	0.130	2.93	3.30
G	0.094 BSC		2.39 BSC	
H	0.050	0.095	1.27	2.41
J	0.015	0.025	0.39	0.63
K	0.575	0.655	14.61	16.63
M	5° TYP		5° TYP	
Q	0.148	0.158	3.76	4.01
R	0.045	0.065	1.15	1.65
S	0.025	0.035	0.64	0.88
U	0.145	0.155	3.69	3.93
V	0.040	---	1.02	---

STYLE 1:
PIN 1. EMITTER
2. COLLECTOR
3. BASE

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada
Fax: 303–675–2176 or 800–344–3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800–282–9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81–3–5773–3850

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative